Peak gate current (t_p=20μs , T_j=125)	I_{GM}	12	A
Average gate power dissipation (T_j=125)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	22	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	1.3	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Value	Unit

ORDERING INFORMATION

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FIG.1: Maximum power dissipation versus RMS on-state current

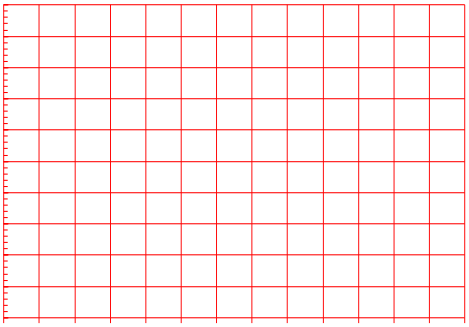
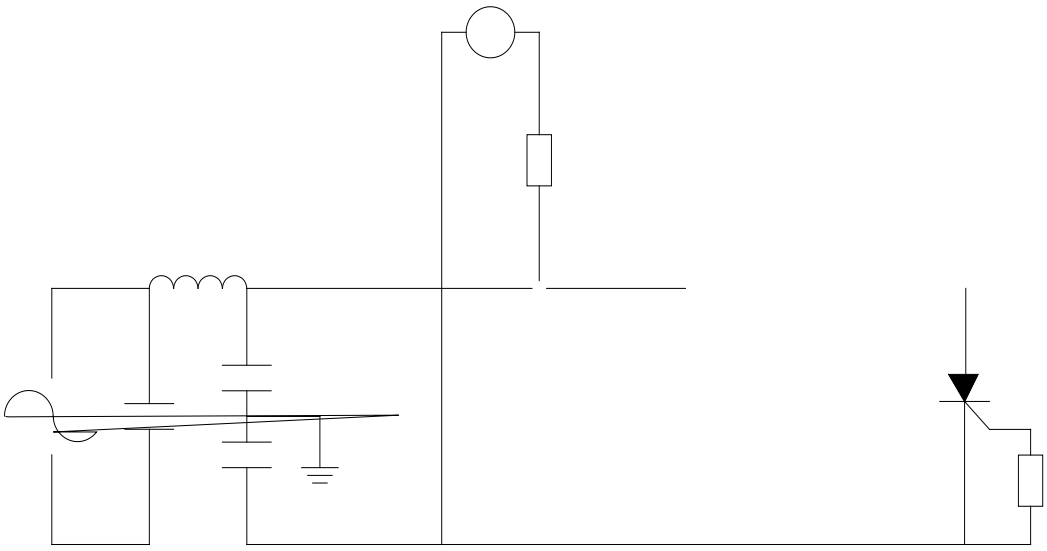
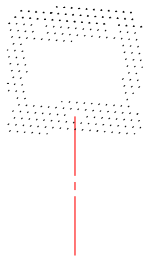


FIG.2: RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



PACKAGE MECHANICAL DATA



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